Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A display device comprising:

a pair of substrates;

an active matrix circuit and a driver circuit provided on one of the pair of substrates;

an insulating film over said driver circuit;

~~a rubbing~~ an orientating film over said insulating film;

a sealing member formed over said ~~rubbing~~ orientating film so as to cover the driver circuit, the sealing member being capable of light blocking; and

an orientating film formed between the sealing member and the other one of the pair of substrates,

wherein the orientating film is in contact with the sealing member, and

wherein the sealing member comprises a pigment for light blocking.

2. (Previously Presented) A display device according to claim 1,

wherein the active matrix circuit has pixels arranged in a matrix form, and

wherein regions in each of the pixels where source lines and drain lines overlap with a pixel electrode form a black matrix.

3. (Previously Presented) A display device according to claim 1,

wherein one of an electrode or a wiring line connected to a source or drain of a thin-film transistor formed in the active matrix circuit is one of a metal film, a semiconductor film, and a silicide film; and

wherein a light blocking film for the thin-film transistor is formed by using the one of the metal film, the semiconductor film, and the silicide film.

4. (Previously Presented) A display device according to claim 1, wherein said pair of substrates are glass substrates or quartz substrates.

5. (Previously Presented) A display device according to claim 1 wherein said pair of substrates are bonded to each other with the sealing member.

6. (Previously Presented) A device according to claim 1 further comprising:

at least a CMOS transistor formed in the driver circuit region, said CMOS transistor having an n-channel thin film transistor and a p-channel thin film transistor;

a thin film transistor formed in each pixel in the active matrix circuit, said thin film transistor having at least an active layer, a gate insulating film adjacent to said active layer, and a gate electrode adjacent to said gate insulating film,

wherein a light block film is formed over said gate electrode.

7. (Previously Presented) A device according to claim 1 further comprising a liquid crystal material interposed between the pair of substrates,

wherein said sealing member seals the liquid crystal material.

8. (Currently Amended) An electronic device comprising:

at least a first substrate and a second substrate;

a driver circuit region formed on said first substrate, said driver circuit region having at least one of a shift register circuit, a NAND circuit, a level shifter circuit and a buffer circuit;

an active matrix region formed on said first substrate, said active matrix region having at least a pixel;

an insulating film over said driver circuit;

~~a rubbing~~ an orientating film over said insulating film;

a sealing member formed between said ~~rubbing~~ orientating film and said second substrate, said sealing member bonding said first and second substrates and covering said driver circuit region; and

an orientating film formed between the sealing member and the second substrate, wherein the orientating film is in contact with said sealing member,

wherein said sealing member shields said driver circuit region from light; and

wherein said sealing member comprises a pigment for light blocking.

9. (Canceled)

10. (Previously Presented) A device according to claim 8 wherein said shift register circuit comprises at least a clocked inverter and an inverter.

11. (Previously Presented) A device according to claim 8 further comprising:

at least a CMOS transistor formed in said driver circuit region, said CMOS transistor having an n-channel thin film transistor and a p-channel thin film transistor;

a thin film transistor formed in said pixel, said thin film transistor having at least an active layer, a gate insulating film adjacent to said active layer, a gate electrode adjacent to said gate insulating film, and further comprising a light blocking film formed over said gate electrode.

12-14. (Canceled)

15. (Previously Presented) A device according to claim 8 further comprising a liquid crystal material injected between the first substrate and the second substrate.

16-21. (Canceled)

22. (Currently Amended) A display device comprising:

a pair of substrates;

an active matrix circuit and a driver circuit provided on one of the pair of substrates;

an insulating film over said driver circuit;

~~a rubbing~~ an orientating film over said insulating film;

a sealing member formed over said ~~rubbing~~ orientating film so as to cover the driver circuit, the sealing member being capable of light blocking; and

an orientating film formed between the sealing member and the other one of the pair of substrates, wherein the orientating film is in contact with the sealing member,

wherein the sealing member comprises a pigment for light blocking; and

the sealing member is not in contact with said one of the pair of substrates.

23. (Previously Presented) A display device according to claim 22,

wherein the active matrix circuit has pixels arranged in a matrix form; and

regions in each of the pixels where source lines and drain lines overlap with a pixel electrode form a black matrix.

24. (Previously Presented) A display device according to claim 22,

wherein one of an electrode or a wiring line connected to a source or drain of a thin-film transistor formed in the active matrix circuit is one of a metal film, a semiconductor film, and a silicide film; and

wherein a light blocking film for the thin-film transistor is formed by using the one of the metal film, the semiconductor film, and the silicide film.

25. (Previously Presented) A display device according to claim 22 wherein said pair of substrates are glass substrates or quartz substrates.

26. (Previously Presented) A display device according to claim 22 wherein said pair of substrates are bonded to each other with the sealing member.

27. (Previously Presented) A device according to claim 22 further comprising:

at least a CMOS transistor formed in the driver circuit region, said CMOS transistor having an n-channel thin film transistor and a p-channel thin film transistor; and

a thin film transistor formed in each pixel in the active matrix circuit, said thin film transistor having at least an active layer, a gate insulating film adjacent to said active layer, a gate electrode adjacent to said gate insulating film,

wherein a light block film is formed over said gate electrode.

28. (Previously Presented) A device according to claim 22 further comprising a liquid crystal material interposed between the pair of substrates,

wherein said sealing member seals the liquid crystal material.

29. (Currently Amended) An electronic device comprising:

at least a first substrate and a second substrate;

a driver circuit region formed on said first substrate, said driver circuit region having at least one of a shift register circuit, a NAND circuit, a level shifter circuit and a buffer circuit;

an active matrix region formed on said first substrate, said active matrix region having at least a pixel;

an insulating film over said driver circuit;

~~a rubbing~~ an orientating film over said insulating film;

a sealing member formed between said ~~rubbing~~ orientating film and said second substrate, said sealing member bonding said first and second substrates and covering said driver circuit region; and

an orientating film formed between said sealing member and the second substrate, wherein the orientating film is in contact with said sealing member,

wherein said sealing member shields said driver circuit region from light;

said sealing member comprises a pigment for light blocking; and

said sealing member is not in contact with said first substrate.

30. (Previously Presented) A device according to claim 29 wherein said shift register circuit comprises at least a clocked inverter and an inverter.

31. (Previously Presented) A device according to claim 29 further comprising:

at least a CMOS transistor formed in said driver circuit region, said CMOS transistor having an n-channel thin film transistor and a p-channel thin film transistor; and

a thin film transistor formed in said pixel, said thin film transistor having at least an active layer, a gate insulating film adjacent to said active layer, a gate electrode adjacent to said gate insulating film, and further comprising a light blocking film formed over said gate electrode.

32. (Previously Presented) A device according to claim 29 further comprising a liquid crystal material injected between the first substrate and the second substrate.

33. (Previously Presented) A device according to claim 1, wherein said insulating film is made of a resin.

34. (Previously Presented) A device according to claim 8, wherein said insulating film is made of a resin.

35. (Canceled)

36. (Previously Presented) A device according to claim 22, wherein said insulating film is made of a resin.

37. (Previously Presented) A device according to claim 29, wherein said insulating film is made of a resin between said driver circuit and said sealing material.